

N-channel 650 V, 0.98 Ω typ., 5 A MDmesh™ M2 Power MOSFETs in TO-220 and IPAK packages

Datasheet - production data

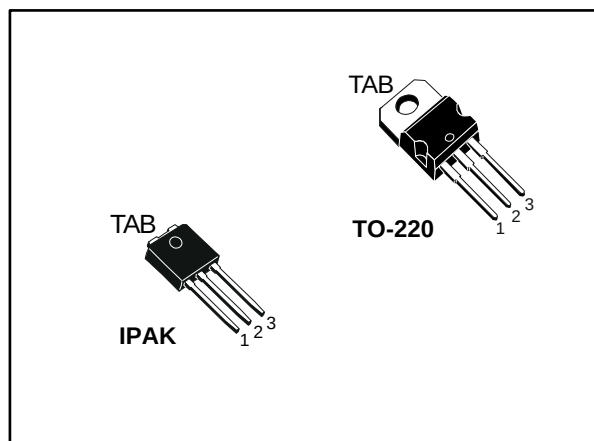
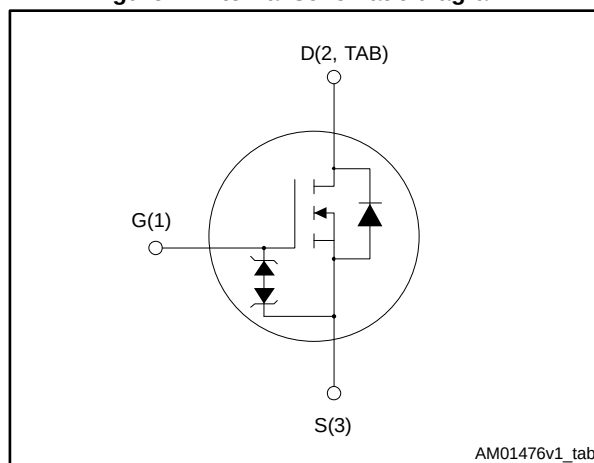


Figure 1: Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)} max	I _D
STP7N65M2	650 V	1.15 Ω	5 A
STU7N65M2	650 V	1.15 Ω	5 A

- Extremely low gate charge
- Excellent output capacitance (C_{oss}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

These devices are N-channel Power MOSFETs developed using the MDmesh™ M2 technology. Thanks to the strip layout associated with an improved vertical structure, the device exhibits both low on-resistance and optimized switching characteristics. It is therefore suitable for the most demanding high efficiency converters.

Table 1: Device summary

Order code	Marking	Package	Packaging
STP7N65M2	7N65M2	TO-220	Tube
STU7N65M2	7N65M2	IPAK	Tube

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	5	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	3.2	A
$I_{DM}^{(1)}$	Drain current (pulsed)	20	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	60	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	50	
T_{stg}	Storage temperature	- 55 to 150	$^{\circ}\text{C}$
T_j	Operating junction temperature		

Notes:

(1) Pulse width limited by safe operating area

(2) $I_{SD} \leq 5\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$; $V_{DSpeak} < V_{(BR)DSS}$, $V_{DD}=400\text{ V}$ (3) $V_{DS} \leq 520\text{ V}$

Table 3: Thermal data

Symbol	Parameter	Value		Unit
		TO-220	IPAK	
$R_{thj-case}$	Thermal resistance junction-case max	2.08		$^{\circ}\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5	100	$^{\circ}\text{C}/\text{W}$

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	1	A
E_{AS}	Single pulse avalanche energy (starting $T_j=25^{\circ}\text{C}$, $I_D=I_{AR}$; $V_{DD}=50\text{ V}$)	103	mJ

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 5: On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} = 0, I _D = 1 mA	650			V
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0, V _{DS} = 650 V			1	μA
		V _{GS} = 0, V _{DS} = 650 V, T _C = 125 °C			100	μA
I _{GSS}	Gate-body leakage current	V _{DS} = 0, V _{GS} = ± 25 V			±10	μA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	2	3	4	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = 2.5 A		0.98	1.15	Ω

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C _{iss}	Input capacitance	V _{DS} = 100 V, f = 1 MHz, V _{GS} = 0	-	270	-	pF
C _{oss}	Output capacitance		-	14.5	-	
C _{rss}	Reverse transfer capacitance		-	0.8	-	
C _{oss eq.} ⁽¹⁾	Equivalent output capacitance	V _{DS} = 0 to 520 V, V _{GS} = 0	-	108	-	pF
R _G	Intrinsic gate resistance	f = 1 MHz open drain	-	7	-	Ω
Q _g	Total gate charge	V _{DD} = 520 V, I _D = 5 A, V _{GS} = 10 V (see Figure 17: "Gate charge test circuit")	-	9	-	nC
Q _{gs}	Gate-source charge		-	2.3	-	nC
Q _{gd}	Gate-drain charge		-	4.3	-	nC

Notes:

⁽¹⁾C_{oss eq.} is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{DD} = 325 V, I _D = 2.5 A, R _G = 4.7 Ω, V _{GS} = 10 V (see Figure 16: "Switching times test circuit for resistive load" and Figure 21: "Switching time waveform")	-	8	-	ns
t _r	Rise time		-	20	-	ns
t _{d(off)}	Turn-off delay time		-	30	-	ns
t _f	Fall time		-	20	-	ns

Table 8: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		20	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 5\text{ A}$, $V_{GS} = 0$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see Figure 21: "Switching time waveform")	-	275		ns
Q_{rr}	Reverse recovery charge		-	1.62		μC
I_{RRM}	Reverse recovery current		-	11.8		A
t_{rr}	Reverse recovery time	$I_{SD} = 5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 21: "Switching time waveform")	-	430		ns
Q_{rr}	Reverse recovery charge		-	2.54		μC
I_{RRM}	Reverse recovery current		-	11.9		A

Notes:⁽¹⁾Pulse width limited by safe operating area.⁽²⁾Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2: Safe operating area for TO-220

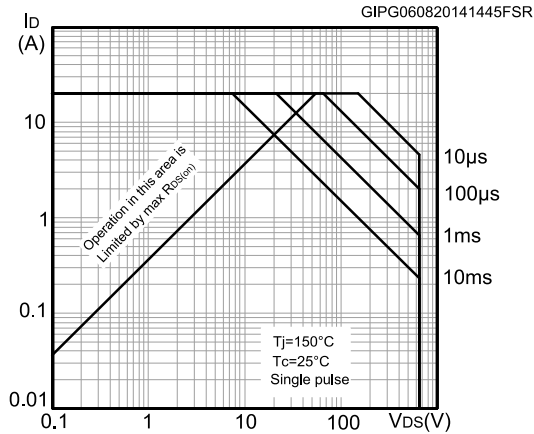


Figure 3: Thermal impedance for TO-220

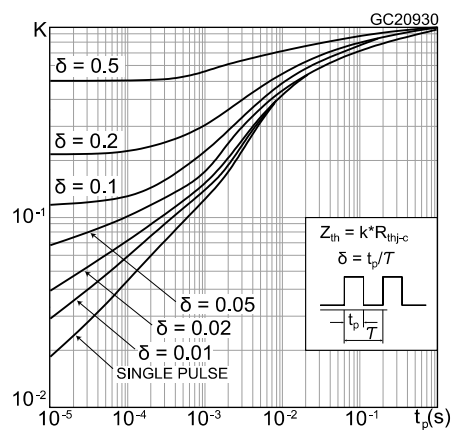


Figure 4: Safe operating area for IPAK

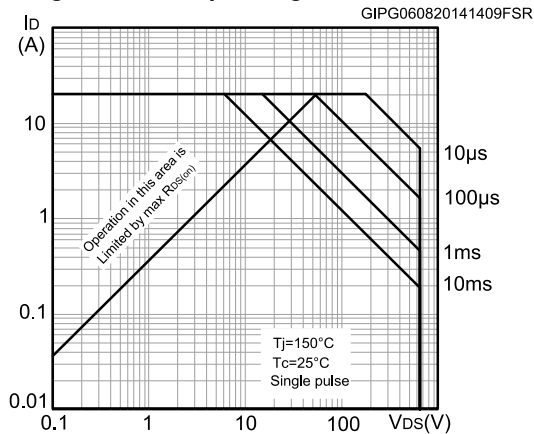


Figure 5: Thermal impedance for IPAK

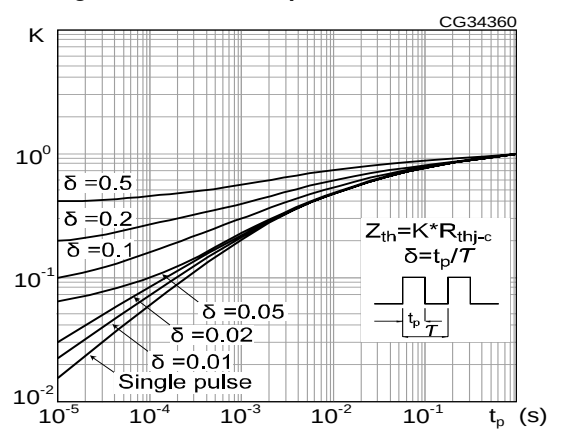


Figure 6: Output characteristics

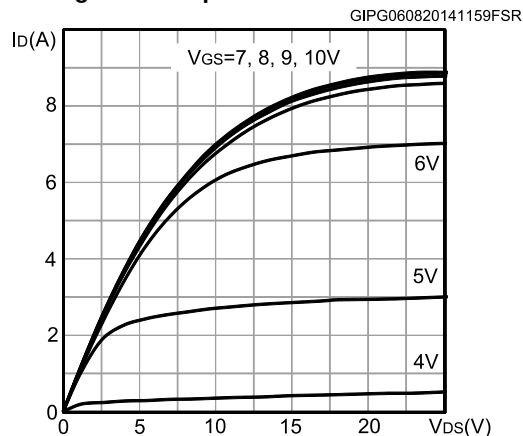


Figure 7: Transfer characteristics

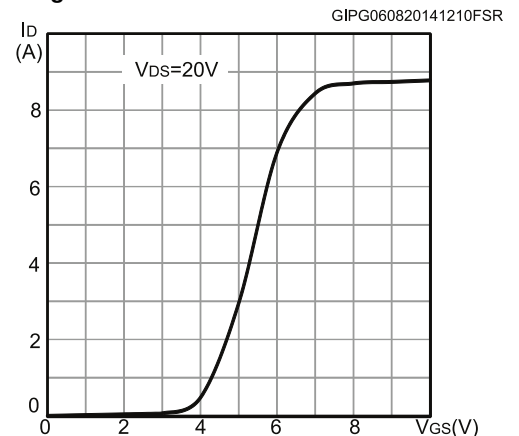


Figure 8: Gate charge vs gate-source voltage

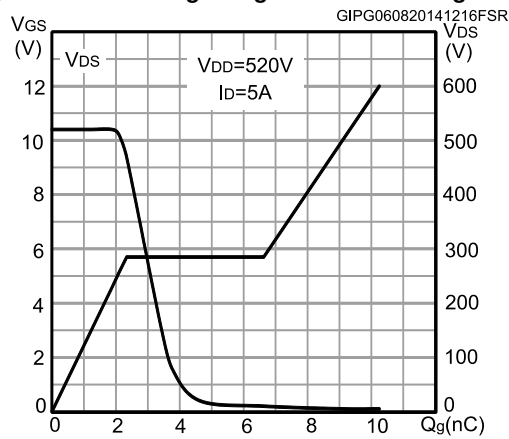


Figure 9: Static drain-source on-resistance

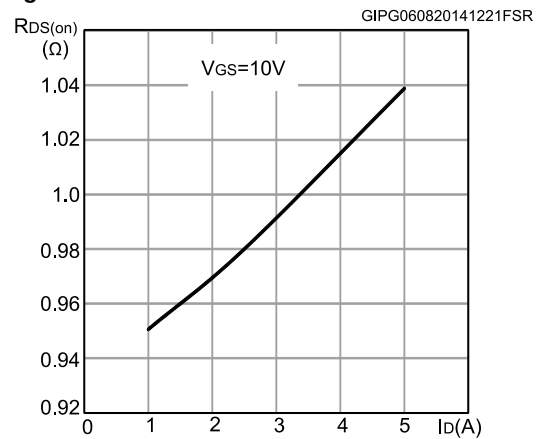


Figure 10: Capacitance variations

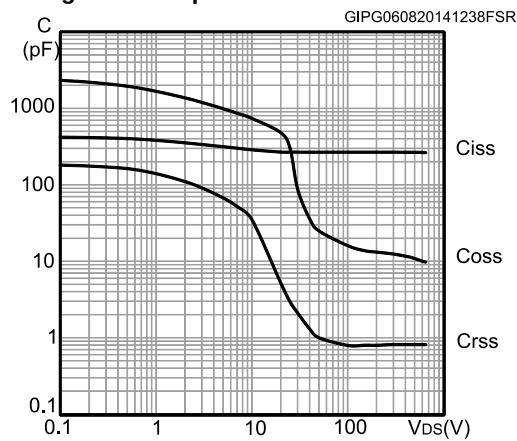


Figure 11: Output capacitance stored energy

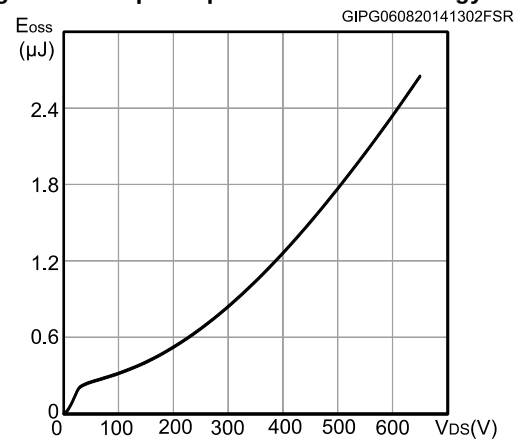


Figure 12: Normalized gate threshold voltage vs temperature

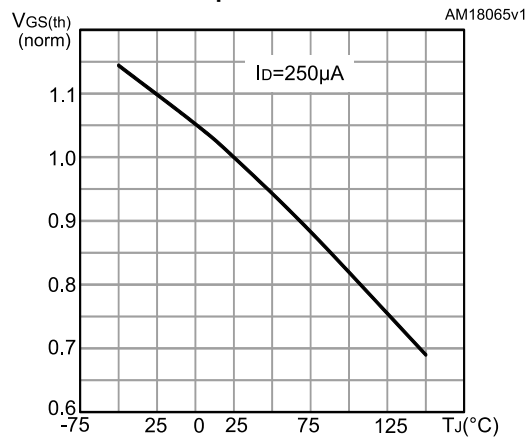


Figure 13: Normalized on-resistance vs temperature

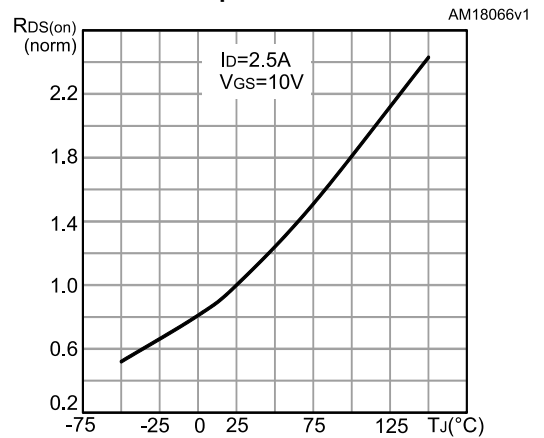
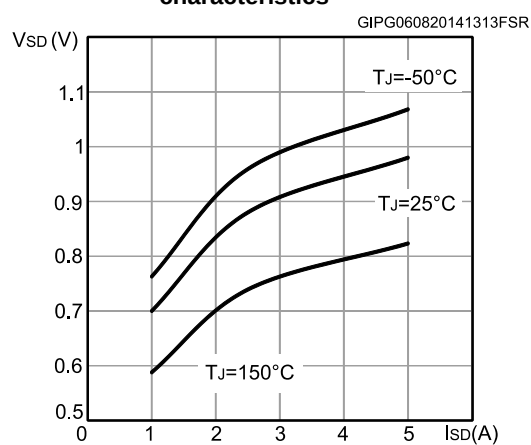
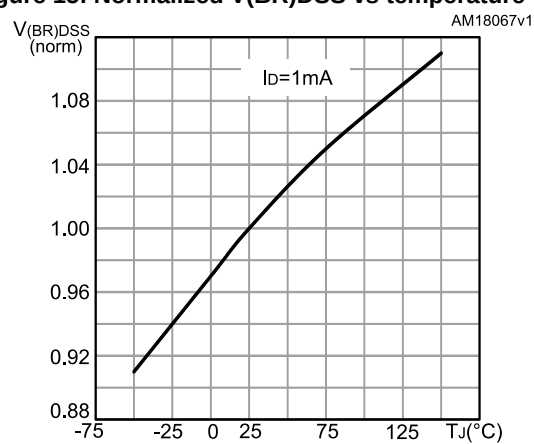
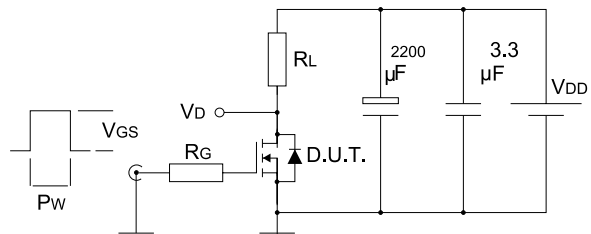


Figure 14: Source-drain diode forward characteristics**Figure 15: Normalized $V_{(BR)DSS}$ vs temperature**

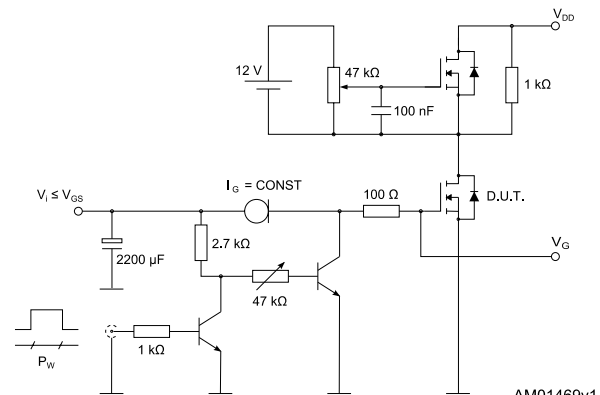
3 Test circuits

Figure 16: Switching times test circuit for resistive load



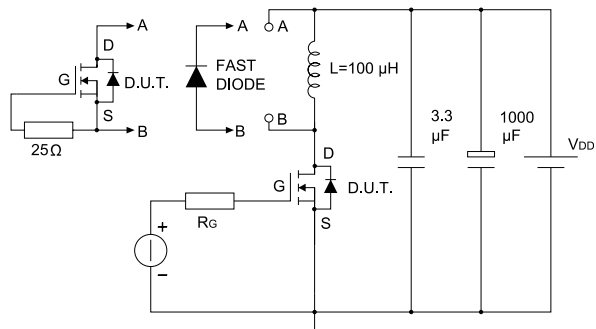
AM01468v1

Figure 17: Gate charge test circuit



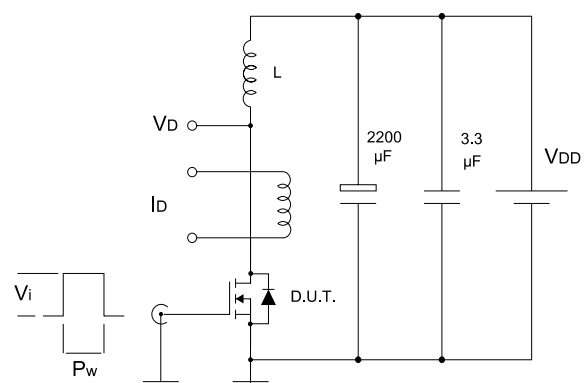
AM01469v1

Figure 18: Test circuit for inductive load switching and diode recovery times



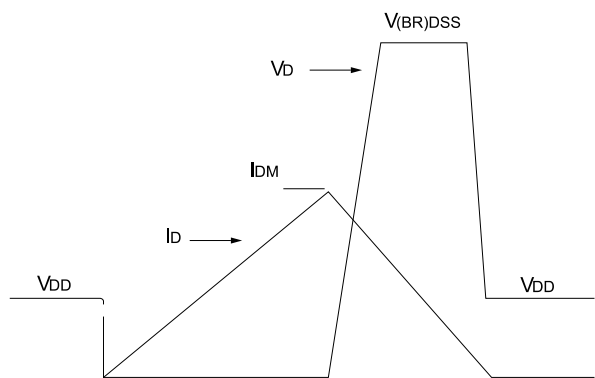
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Figure 19: Unclamped inductive load test circuit



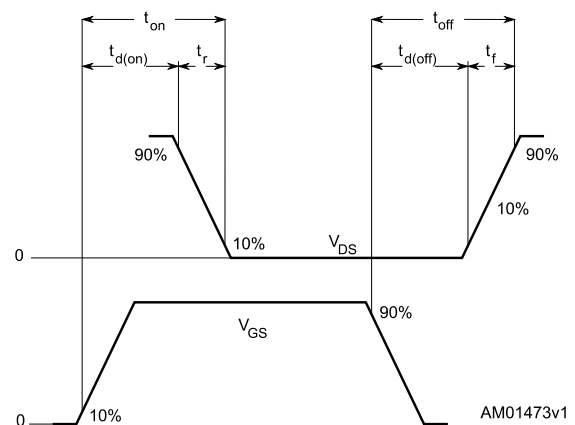
AM01471v1

Figure 20: Unclamped inductive waveform



AM01472v1

Figure 21: Switching time waveform



AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK[®] is an ST trademark.

4.1 TO-220 type A package information

Figure 22: TO-220 type A package outline

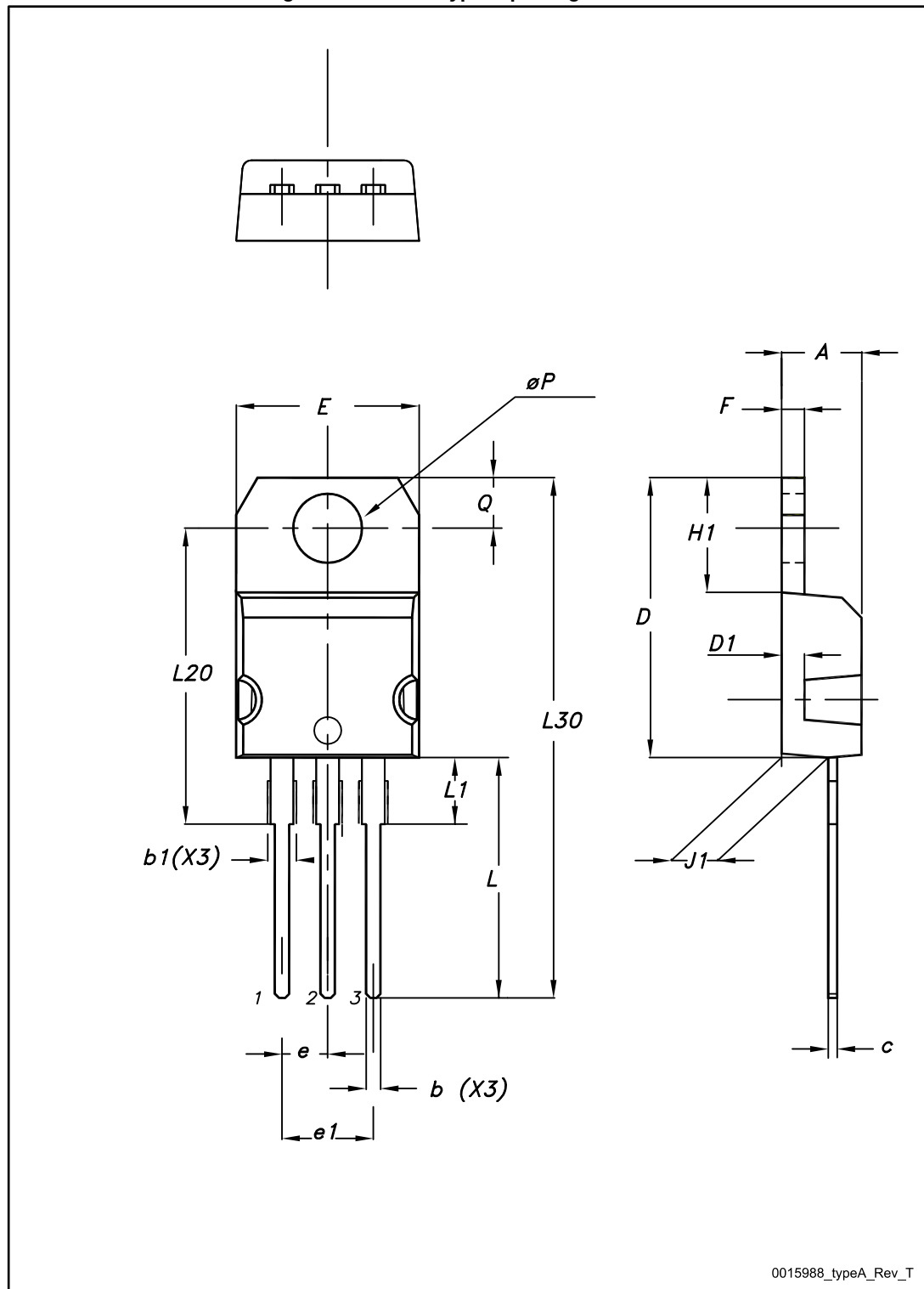


Table 9: TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

4.2 IPAK(TO-251) type A package information

Figure 23: IPAK (TO-251) type A package outline

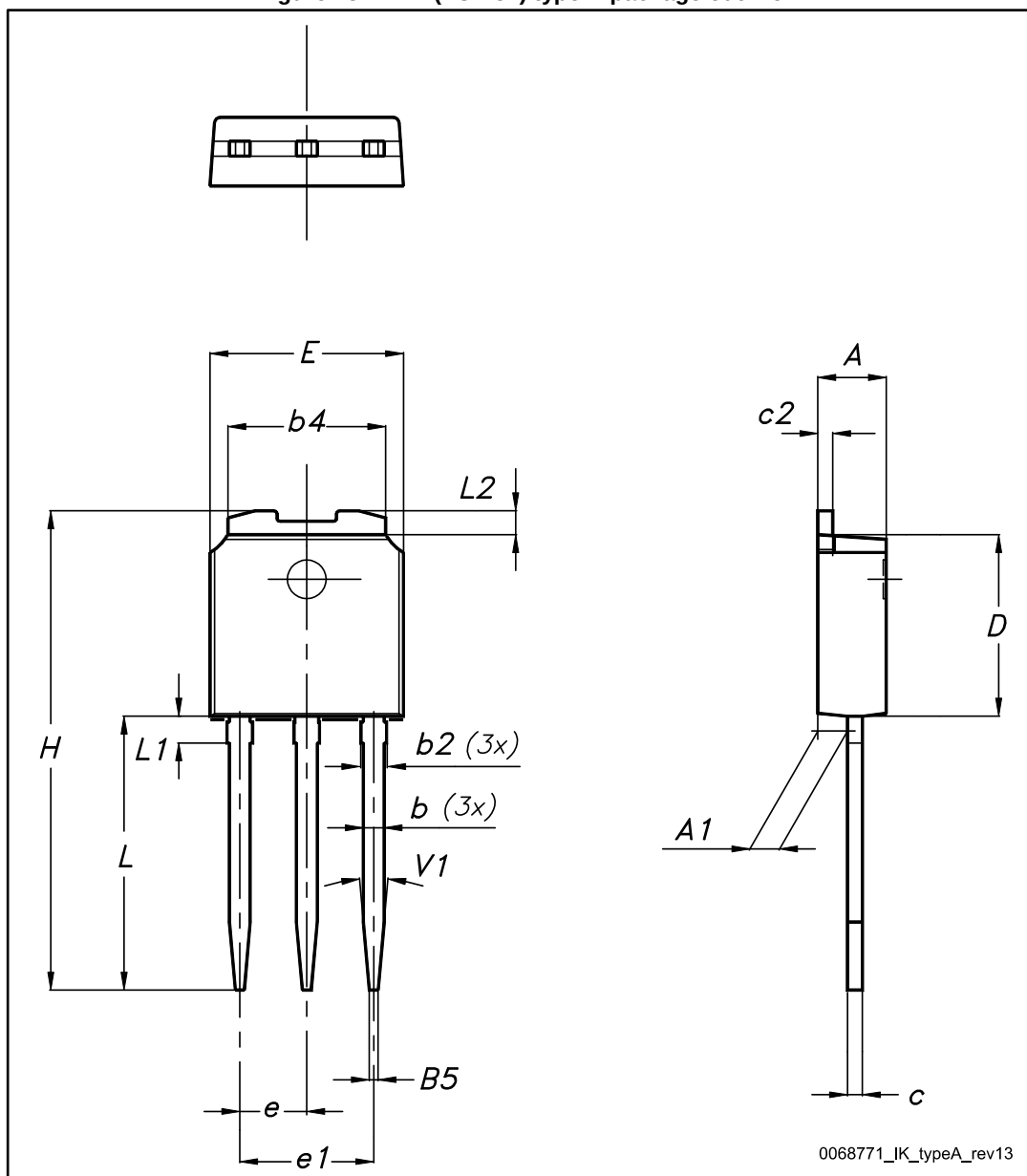


Table 10: IPAK (TO-251) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

4.3 IPAK (TO-251) type C package information

Figure 24: IPAK (TO-251) type C package outline

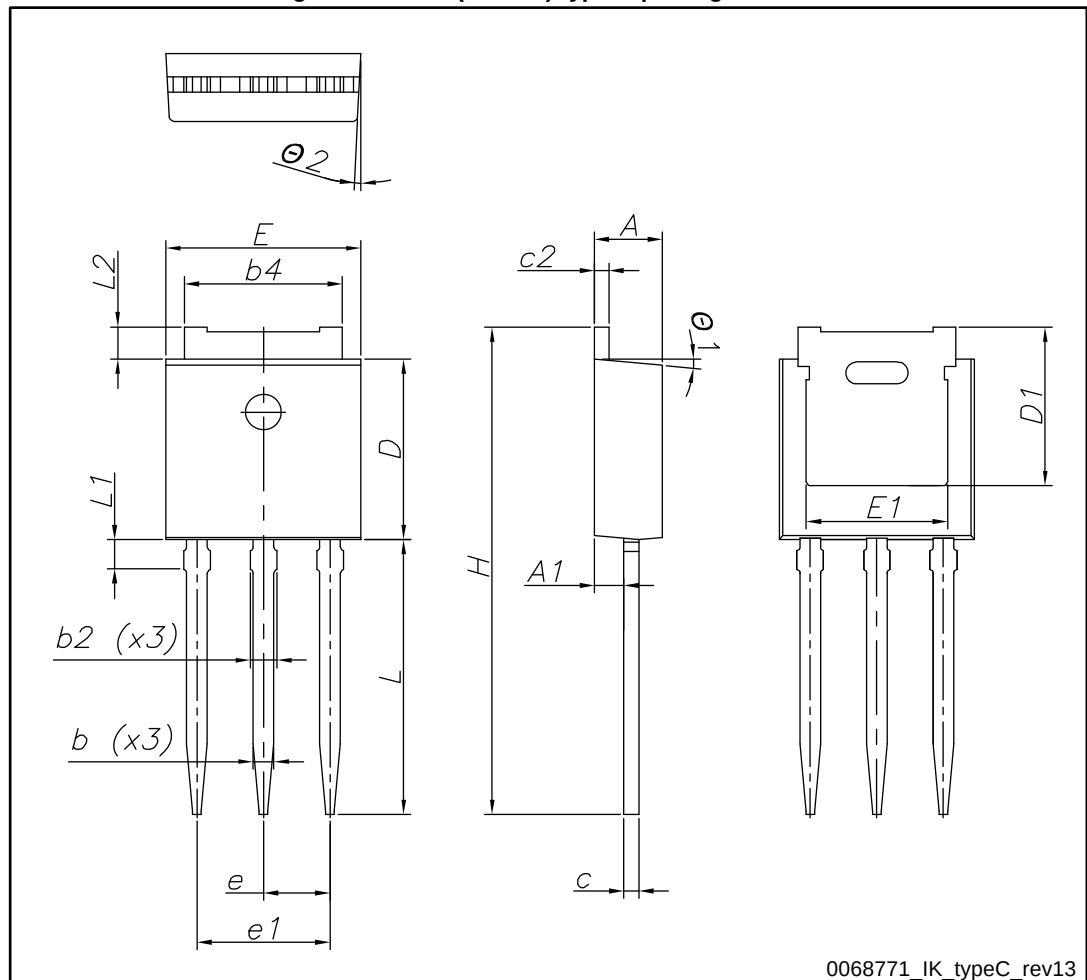


Table 11: IPAK (TO-251) type C package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.35
A1	0.90	1.00	1.10
b	0.66		0.79
b2			0.90
b4	5.23	5.33	5.43
c	0.46		0.59
c2	0.46		0.59
D	6.00	6.10	6.20
D1	5.20	5.37	5.55
E	6.50	6.60	6.70
E1	4.60	4.78	4.95
e	2.20	2.25	2.30
e1	4.40	4.50	4.60
H	16.18	16.48	16.78
L	9.00	9.30	9.60
L1	0.90	1.00	1.20
L2	0.90	1.08	1.25
θ1	3°	5°	7°
θ2	1°	3°	5°

5 Revision history

Table 12: Document revision history

Date	Revision	Changes
07-Aug-2014	1	First release.
09-Oct-2014	2	Added and . Updated not found. Minor text changes.
28-May-2015	3	Document status promoted from preliminary to production data. Updated package information.

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